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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/830,049	04/23/2004	Masami Ohnishi	520.43783X00	8728
20457	7590 04/14/2006		EXAM	INER
	I, TERRY, STOUT &	NGUYEN, LINH V		
1300 NORTH SEVENTEENTH STREET SUITE 1800		ART UNIT	PAPER NUMBER	
••••	, VA 22209-3873		2819	

DATE MAILED: 04/14/2006

Please find below and/or attached an Office communication concerning this application or proceeding.

	Application No.	Applicant(s)					
	10/830,049	OHNISHI ET AL.					
Office Action Summary	Examiner	Art Unit					
	Linh V. Nguyen	2819					
The MAILING DATE of this communication app Period for Reply	ears on the cover sheet with the c	orrespondence address					
A SHORTENED STATUTORY PERIOD FOR REPLY WHICHEVER IS LONGER, FROM THE MAILING DA  - Extensions of time may be available under the provisions of 37 CFR 1.13 after SIX (6) MONTHS from the mailing date of this communication.  - If NO period for reply is specified above, the maximum statutory period w.  - Failure to reply within the set or extended period for reply will, by statute, Any reply received by the Office later than three months after the mailing earned patent term adjustment. See 37 CFR 1.704(b).	ATE OF THIS COMMUNICATION  16(a). In no event, however, may a reply be tin  rill apply and will expire SIX (6) MONTHS from  cause the application to become ABANDONE	N. nely filed the mailing date of this communication. D (35 U.S.C. § 133).					
Status							
1)⊠ Responsive to communication(s) filed on 23 Ja	nuan/ 2006						
<del></del>	This action is <b>FINAL</b> . 2b) This action is non-final.  Since this application is in condition for allowance except for formal matters, prosecution as to the merits is						
closed in accordance with the practice under Ex parte Quayle, 1935 C.D. 11, 453 O.G. 213.							
Disposition of Claims							
4)⊠ Claim(s) <u>1-7</u> is/are pending in the application.							
4a) Of the above claim(s) is/are withdrawn from consideration.							
5) Claim(s) is/are allowed.							
6)⊠ Claim(s) <u>1-7</u> is/are rejected.							
7) Claim(s) is/are objected to.	•						
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	olootion requirement.						
Application Papers							
9)☐ The specification is objected to by the Examine							
10)☐ The drawing(s) filed on is/are: a)☐ accepted or b)☐ objected to by the Examiner.							
Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).							
Replacement drawing sheet(s) including the correction is required if the drawing(s) is objected to. See 37 CFR 1.121(d).							
11) The oath or declaration is objected to by the Examiner. Note the attached Office Action or form PTO-152.							
Priority under 35 U.S.C. § 119							
12)⊠ Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).							
a)⊠ All b)☐ Some * c)☐ None of:							
<ol> <li>Certified copies of the priority documents</li> </ol>	1. Certified copies of the priority documents have been received.						
<ol><li>Certified copies of the priority documents</li></ol>	2. Certified copies of the priority documents have been received in Application No						
<ol><li>Copies of the certified copies of the prior</li></ol>	3. Copies of the certified copies of the priority documents have been received in this National Stage						
application from the International Bureau	application from the International Bureau (PCT Rule 17.2(a)).						
* See the attached detailed Office action for a list of the certified copies not received.							
Attachment(s)	_						
1) Notice of References Cited (PTO-892)	4) Interview Summary (PTO-413)						
2) Notice of Draftsperson's Patent Drawing Review (PTO-948) 3) Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08) Paper No(s)/Mail Date		Paper No(s)/Mail Date  Notice of Informal Patent Application (PTO-152)  Other:					

## **DETAILED ACTION**

1. This office action is in response to communication filed on 1/23/06. Claims 1- 7 are pending on this application.

## Response to Arguments

2. Applicant's arguments with respect to claim 1 and 7 have been considered but are most in view of the new ground(s) of rejection.

## Claim Rejections - 35 USC § 102

3. The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

- (b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.
- 4. Claims 1 6 are rejected under 35 U.S.C. 102(b) as being anticipated by Miyazawa U.S. patent No. 6,456125.

Regarding claim 1, Fig. 2A, 2B of Miyazaka disclose radio frequency amplifier module, comprising: a module substrate (20B); a radio frequency power amplifier (23A, 23B) part which is arranged on said module substrate and amplifies a power of a radio frequency signal (IN); a bias control part (G, DB) which is arranged on said module substrate and controls operation of said radio frequency power amplifier part with a bias voltage (B, DB, 32); and a bias supply line (Bonding wires from G, DB) for supplying the bias voltage from said bias control part (G, DB) to said radio frequency power amplifier

part (MMIC), wherein said bias supply line includes at least one bonding pad (32) having a capacitance (30A, 30B) component to a ground and a bonding wire (Bond wires See Fig. 2B) formed via said at least one bonding pad (See Fig. 2B).

Regarding claim 2, wherein said radio frequency power amplifier part (MMIC) is constituted as a semiconductor integrated circuit (MMIC) formed on a semiconductor substrate (20B) and said bias supply line (G, DB, 32) is formed on said semiconductor substrate (20B).

Regarding claim 3, wherein said bias control part (G, DB) is constituted as a semiconductor integrated circuit formed on a semiconductor substrate (20B) and said bias supply line (32) is formed on said semiconductor substrate (20B).

Regarding claim 4, wherein said radio frequency power amplifier part (23A, 23B) and said bias control part (G, DB) are constituted as a semiconductor integrated circuit formed on the same semiconductor substrate (20B) and said bias supply line (Bonding wires) is formed on said semiconductor substrate (20B).

Regarding claim 5, wherein said bias supply line (Bonding wires) is formed on said module substrate (20B).

Regarding claim 6, Fig. 2B further comprising: a second substrate (MMIC) formed on said module substrate (20B), wherein one part of a plurality of bonding pads included in said at least one bonding pad is formed on said module substrate (G, DB) and the other part of said plurality of bonding pads (32, 30B, 25) is formed on said second substrate (MMIC).

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5. Claim 7 is rejected under 35 U.S.C. 102(b) as being anticipated by Heal et al. U.S. Patent No. 5,973,567

Fig. 1 of Heal et al. discloses a module substrate (14); a radio frequency power amplifier part (Q1)) that is arranged on said module substrate (14) and amplifies a power of a radio frequency signal (10); a bias control part (Col. 2 lines 1 – 4) that is arranged on said module substrate (14) and controls operation of said radio frequency power amplifier (23A, 23B) part with a bias voltage (Column 4 lines 30 – 32); and a bias supply line (Col. 2 lines 1 – 4) for supplying the bias voltage from said bias control part (Column 4 lines 30 – 32) to said radio frequency power amplifier part (Q1), wherein said bias supply line (Bonding wires) comprises a low pass filter (Col. 2 lines 9 – 15) which brings attenuation to a radio frequency signal leaking from said radio frequency power amplifier part to said bias control part (this is a intrinsic characteristic of bond wires having low pass filter; Hence, Heal et al. as applied above taught an amplifier having bias bond wires comprising low pass filter; therefore brings attenuation to a radio frequency signal leaking from said radio frequency power amplifier is intrinsic to power amplifier of Heal et al.).

## Conclusion

5. The prior art made of record and not relied upon is considered pertinent to applicant's disclosure.

#### **Contact Information**

6. Any inquiry concerning this communication or earlier communications from the

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examiner should be directed to Linh Van Nguyen whose telephone number is (571) 272-1810. The examiner can normally be reached from 8:30 – 5:00 Monday-Friday. If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Mr. Rexford Barnie can be reached at (571) 272-7492. The fax phone numbers for the organization where this application or proceeding is assigned are (571-273-8300) for regular communications and (571-273-8300) for After Final communications.

4/5/06

´ LINH NGUYEN PRIMARY FXAMINEF

Linh Van Nguyen

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